

Mustafa Alevli

List of Publications by Year in descending order

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Version: 2024-02-01

29
papers

648
citations

686830

13
h-index

552369

26
g-index

30
all docs

30
docs citations

30
times ranked

677
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural properties of AlN films deposited by plasma-enhanced atomic layer deposition at different growth temperatures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 266-271.	0.8	111
2	Self-limiting low-temperature growth of crystalline AlN thin films by plasma-enhanced atomic layer deposition. <i>Thin Solid Films</i> , 2012, 520, 2750-2755.	0.8	86
3	Atomic layer deposition of GaN at low temperatures. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, 01A124.	0.9	62
4	The influence of N ₂ /H ₂ and ammonia N source materials on optical and structural properties of AlN films grown by plasma enhanced atomic layer deposition. <i>Journal of Crystal Growth</i> , 2011, 335, 51-57.	0.7	47
5	Characterization of InN layers grown by high-pressure chemical vapor deposition. <i>Applied Physics Letters</i> , 2006, 89, 112119.	1.5	39
6	Optical properties of AlN thin films grown by plasma enhanced atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, .	0.9	33
7	A Near-Infrared Range Photodetector Based on Indium Nitride Nanocrystals Obtained Through Laser Ablation. <i>IEEE Electron Device Letters</i> , 2014, 35, 936-938.	2.2	33
8	Enhanced memory effect via quantum confinement in 16%nm InN nanoparticles embedded in ZnO charge trapping layer. <i>Applied Physics Letters</i> , 2014, 104, 253106.	1.5	27
9	Comparison of trimethylgallium and triethylgallium as Ga-source materials for the growth of ultrathin GaN films on Si (100) substrates via hollow-cathode plasma-assisted atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, 01A137.	0.9	24
10	The characterization of InN growth under high-pressure CVD conditions. <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, 2985-2994.	0.7	23
11	Substrate temperature influence on the properties of GaN thin films grown by hollow-cathode plasma-assisted atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	0.9	19
12	Surface electron accumulation in indium nitride layers grown by high pressure chemical vapor deposition. <i>Surface Science</i> , 2007, 601, L120-L123.	0.8	18
13	Role of film thickness on the structural and optical properties of GaN on Si (100) grown by hollow-cathode plasma-assisted atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	0.9	17
14	Generation of InN nanocrystals in organic solution through laser ablation of high pressure chemical vapor deposition-grown InN thin film. <i>Journal of Nanoparticle Research</i> , 2012, 14, 1.	0.8	13
15	Influence of N ₂ /H ₂ and N ₂ plasma on binary III-nitride films prepared by hollow-cathode plasma-assisted atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	0.9	13
16	The Fermi level dependence of the optical and magnetic properties of Ga _{1-x} Mn _x N grown by metal-organic chemical vapour deposition. <i>Journal of Physics Condensed Matter</i> , 2006, 18, 2615-2622.	0.7	12
17	Performance improvements of ultraviolet/infrared dual-band detectors. <i>Infrared Physics and Technology</i> , 2007, 50, 142-148.	1.3	12
18	Surface structure, composition, and polarity of indium nitride grown by high-pressure chemical vapor deposition. <i>Applied Physics Letters</i> , 2006, 88, 122112.	1.5	11

#	ARTICLE	IF	CITATIONS
19	Thermal stability of InN epilayers grown by high pressure chemical vapor deposition. Applied Surface Science, 2013, 268, 1-5.	3.1	11
20	Optical properties of InN grown on templates with controlled surface polarities. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2351-2354.	0.8	7
21	Enhancement of polycrystalline silicon solar cells efficiency using indium nitride particles. Journal of Optics (United Kingdom), 2015, 17, 105903.	1.0	7
22	Enhancement in c-Si solar cells using 16 nm InN nanoparticles. Materials Research Express, 2016, 3, 056202.	0.8	6
23	Effect of N ₂ /H ₂ plasma on the growth of InN thin films on sapphire by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	6
24	Visible/infrared refractive index and phonon properties of GaN films grown on sapphire by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 050901.	0.9	5
25	Effect of reactor pressure on optical and electrical properties of InN films grown by high-pressure chemical vapor deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 423-429.	0.8	3
26	Properties of InN grown by High-Pressure CVD. Materials Research Society Symposia Proceedings, 2005, 892, 64.	0.1	1
27	Effect of substrate temperature and Ga source precursor on growth and material properties of GaN grown by hollow cathode plasma assisted atomic layer deposition. , 2016, , .		1
28	The growth of InN and related alloys by high-pressure CVD. , 2005, , .		0
29	Properties of InN layers grown by High Pressure CVD. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0